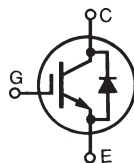


# High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

## IXBT22N300HV IXBH22N300HV



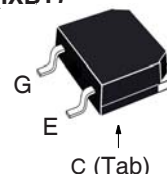
$$V_{CES} = 3000V$$

$$I_{C110} = 22A$$

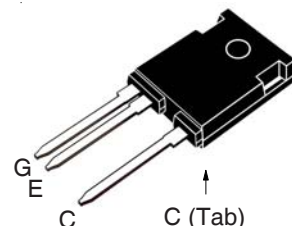
$$V_{CE(sat)} \leq 2.7V$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	3000	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	60	A
$I_{C110}$	$T_C = 110^\circ C$	22	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	190	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 15\Omega$ Clamped Inductive Load	$I_{CM} = 180$ $V_{CES} \leq 1500$	A V
<b><math>T_{SC}</math></b> <b>(SCSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 52\Omega$ , $V_{CE} = 1500V$ , Non-Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	290	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
<b>Weight</b>	TO-268HV	4	g
	TO-247HV	6	g

TO-268HV (IXBT)



TO-247HV (IXBH)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

### Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 1.5 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 22A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		2.2	2.7 V
			2.7	V

Symbol Test Conditions		Characteristic Values		
(T <sub>J</sub> = 25°C Unless Otherwise Specified)		Min.	Typ.	Max.
<b>g<sub>FS</sub></b>	I <sub>C</sub> = 22A, V <sub>CE</sub> = 10V, Note 1	13	22	S
<b>C<sub>ies</sub></b>	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz		2200	pF
<b>C<sub>oes</sub></b>			85	pF
<b>C<sub>res</sub></b>			30	pF
<b>Q<sub>g(on)</sub></b>	I <sub>C</sub> = 22A, V <sub>GE</sub> = 15V, V <sub>CE</sub> = 1500V		110	nC
<b>Q<sub>ge</sub></b>			13	nC
<b>Q<sub>gc</sub></b>			45	nC
<b>t<sub>d(on)</sub></b>	<b>Resistive Switching Times, T<sub>J</sub> = 25°C</b>		46	ns
<b>t<sub>r</sub></b>		I <sub>C</sub> = 22A, V <sub>GE</sub> = 15V	360	ns
<b>t<sub>d(off)</sub></b>		V <sub>CE</sub> = 960V, R <sub>G</sub> = 15Ω	205	ns
<b>t<sub>f</sub></b>			1820	ns
<b>t<sub>d(on)</sub></b>	<b>Resistive Switching Times, T<sub>J</sub> = 125°C</b>		43	ns
<b>t<sub>r</sub></b>		I <sub>C</sub> = 22A, V <sub>GE</sub> = 15V	700	ns
<b>t<sub>d(off)</sub></b>		V <sub>CE</sub> = 960V, R <sub>G</sub> = 15Ω	220	ns
<b>t<sub>f</sub></b>			1650	ns
<b>R<sub>thJC</sub></b>				0.43 °C/W
<b>R<sub>thCS</sub></b>	TO-247HV	0.21		°C/W

### Reverse Diode

Symbol Test Conditions		Characteristic Values		
(T <sub>J</sub> = 25°C Unless Otherwise Specified)		Min.	Typ.	Max
<b>V<sub>F</sub></b>	I <sub>F</sub> = 22A, V <sub>GE</sub> = 0V, Note 1			2.7 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 11A, V <sub>GE</sub> = 0V, -di <sub>F</sub> /dt = 100A/μs		1.4	μs
<b>I<sub>RM</sub></b>		V <sub>R</sub> = 100V, V <sub>GE</sub> = 0V		30
<b>Q<sub>RM</sub></b>			21	μC

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

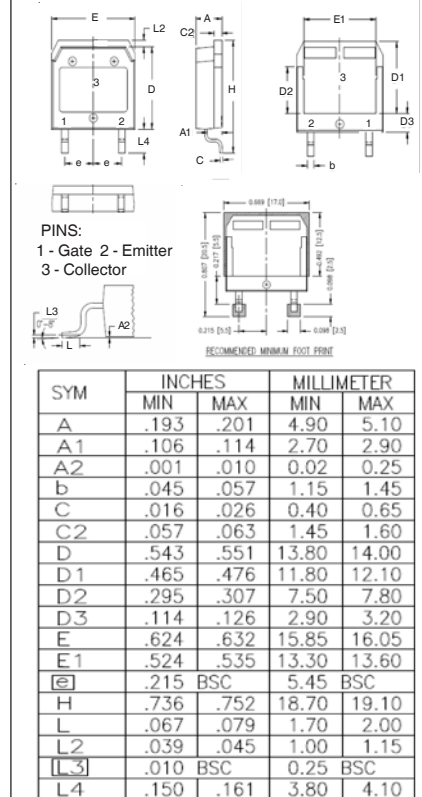
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

### TO-268HV Outline



### TO-247HV Outline

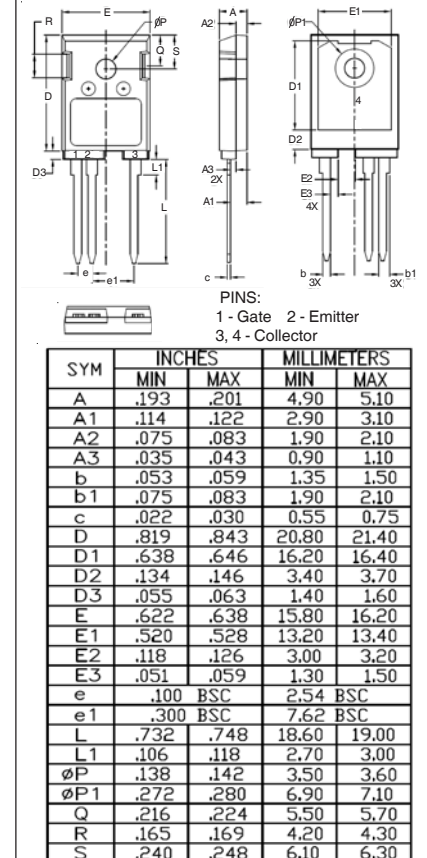


Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

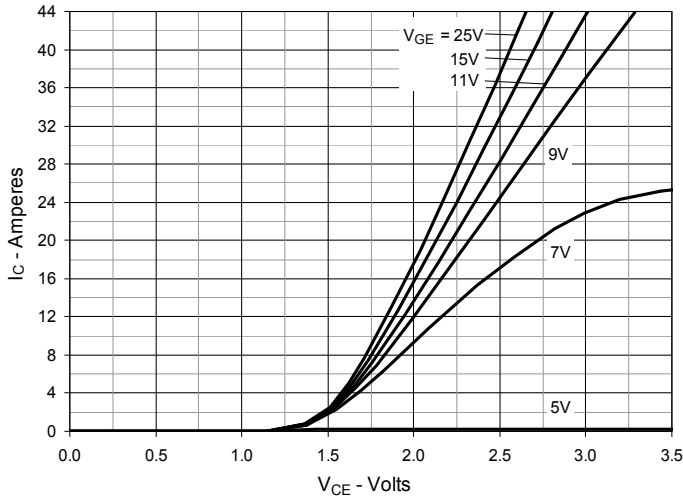


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

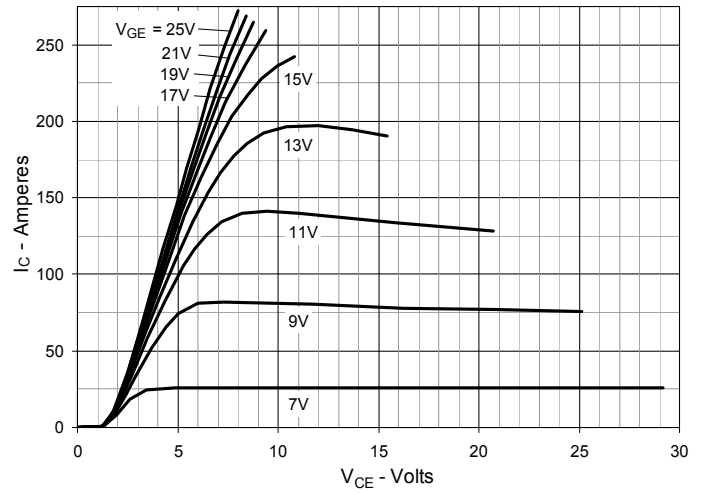


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

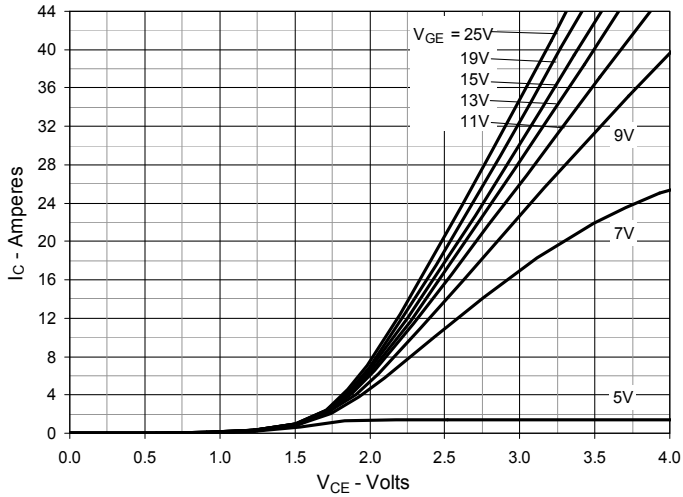


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

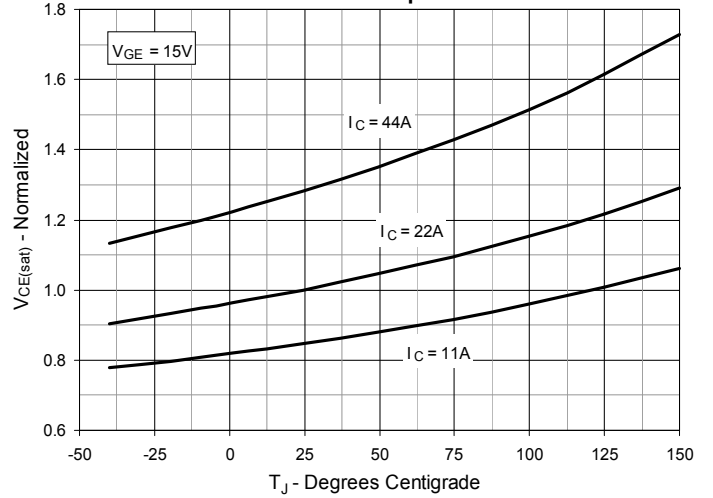


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

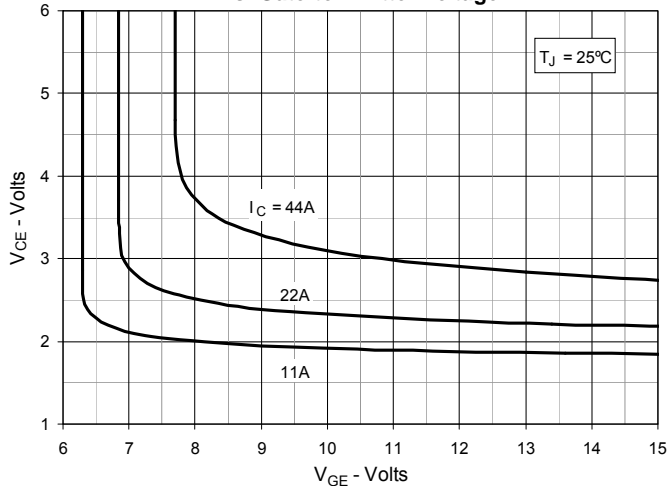


Fig. 6. Input Admittance

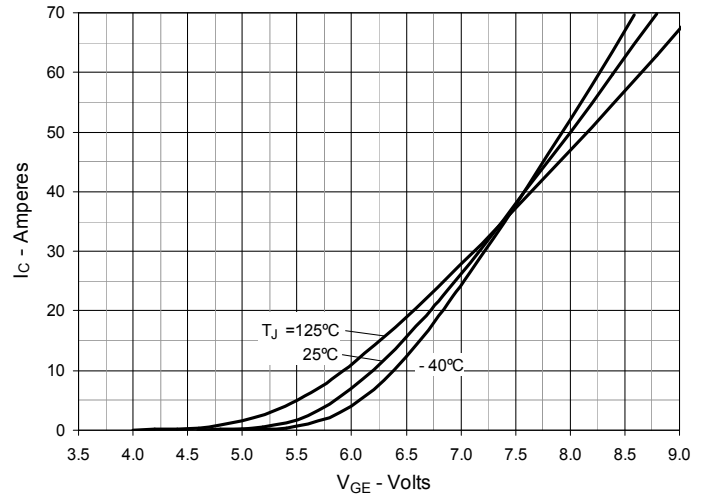


Fig. 7. Transconductance

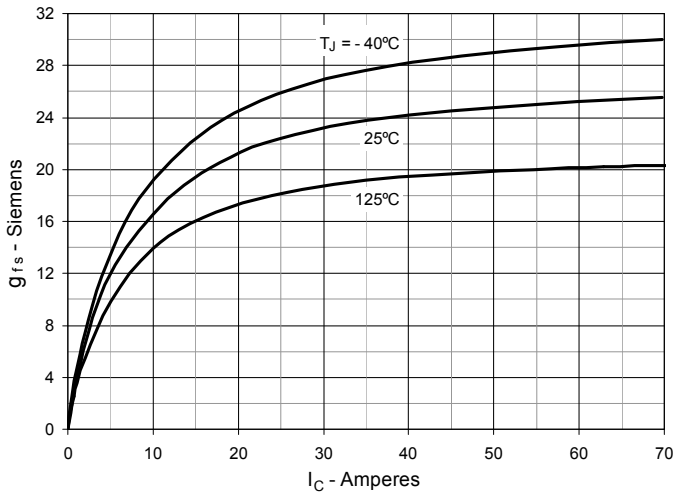


Fig. 8. Gate Charge

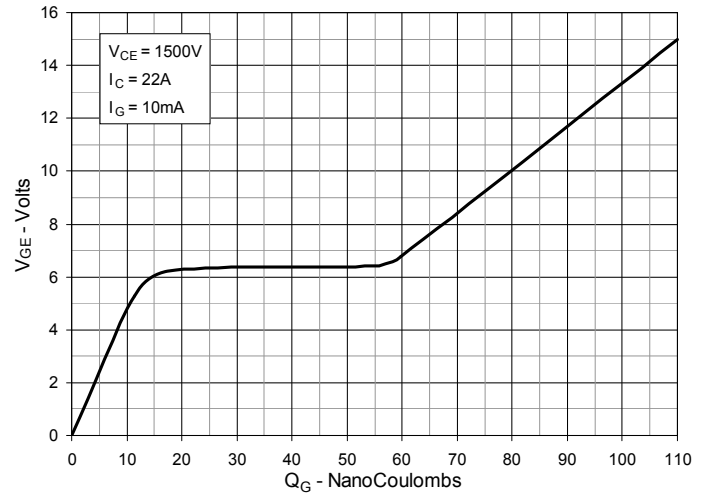


Fig. 9. Forward Voltage Drop of Intrinsic Diode

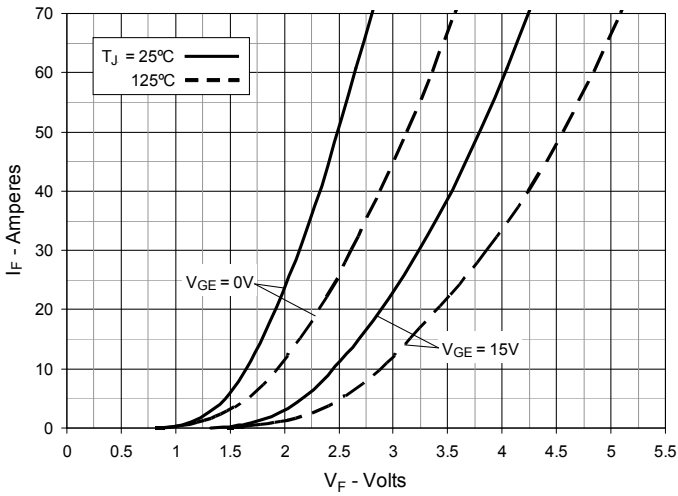


Fig. 10. Capacitance

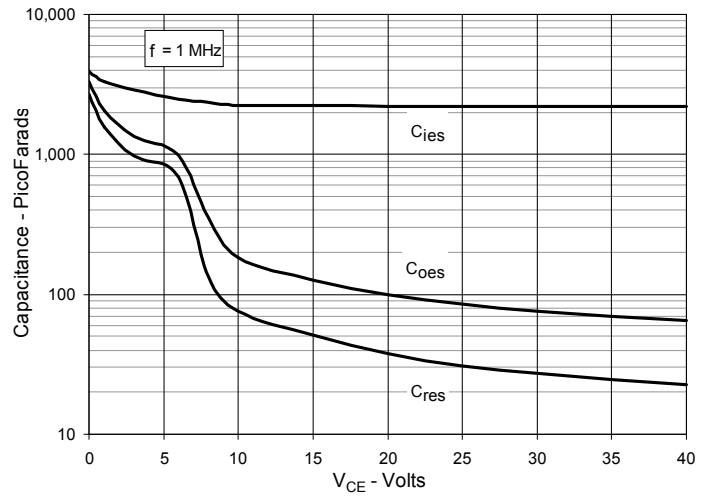


Fig. 11. Reverse-Bias Safe Operating Area

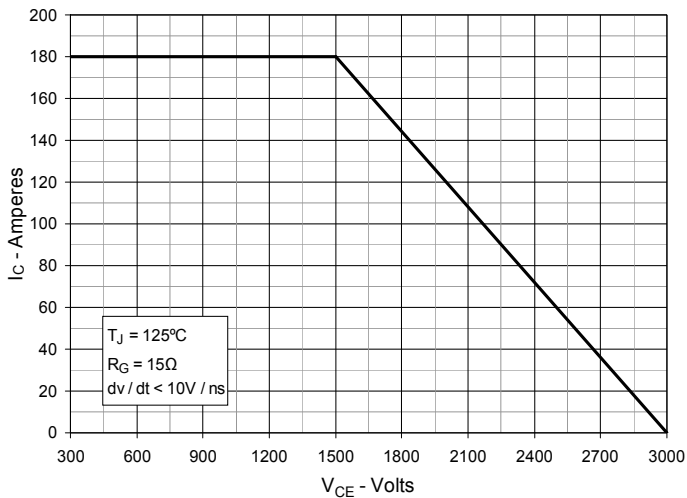


Fig. 12. Maximum Transient Thermal Impedance

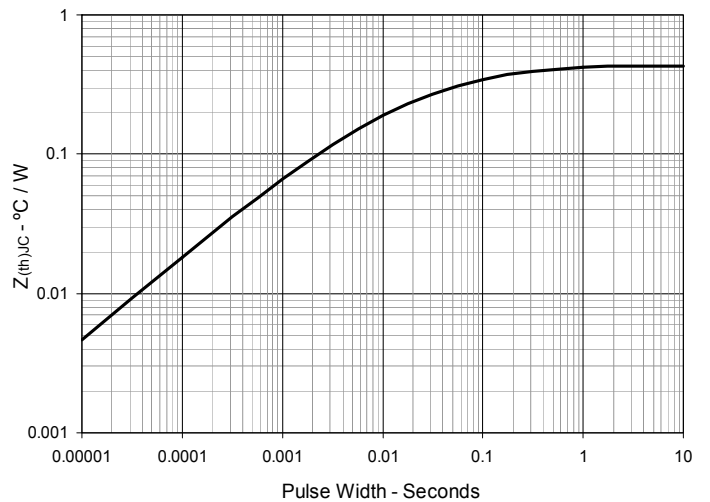


Fig. 13. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$

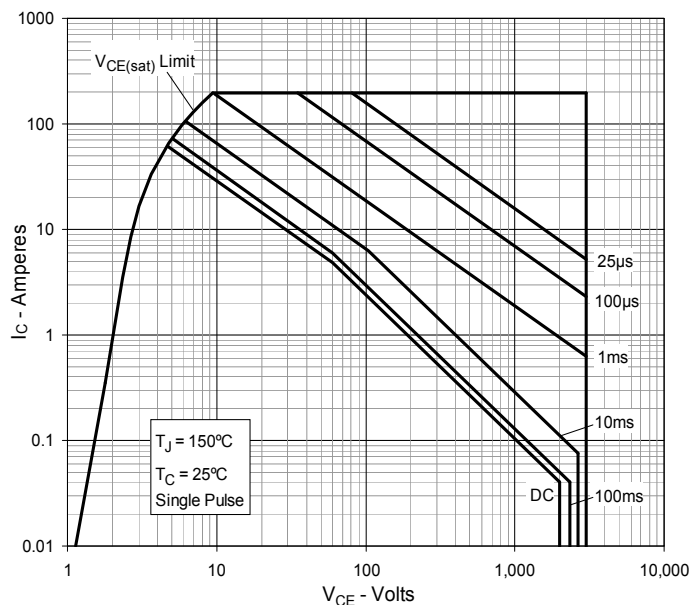
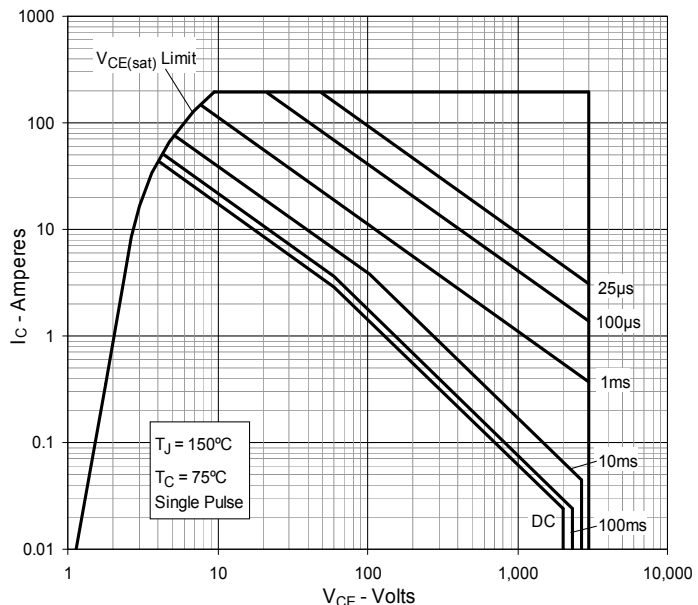


Fig. 14. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$





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